



*#10/Election*  
PATENT  
Customer No. 24852  
Attorney Docket No. 06484.9073  
*9/26/02*

IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

In re Application of: )  
Shi-Tron LIN ) Group Art Unit: 2822  
Serial No.: 09/740,017 ) Examiner: S. Meier  
Filed: December 20, 2000 )  
For: TRANSISTOR STRUCTURE FOR )  
ELECTROSTATIC DISCHARGE )  
PROTECTION CIRCUIT )

Commissioner for Patents and Trademarks  
Washington, DC 20231

Sir:

**RESPONSE TO SPECIES ELECTION REQUIREMENT**

In a species election requirement dated June 4, 2002, the period for response to which has been extended through October 4, 2002 by a request for three-month extension and fee payment filed concurrently herewith, the Examiner required election under 35 U.S.C. § 121.

The Examiner required election between the following species:

Group I, characterized by the Examiner as drawn to an ESD structure having at least one island along a length direction of a first diffusion positioned in non-symmetrical fashion;

Group II, characterized by the Examiner as drawn to an ESD structure having only one island along a length direction of a first diffusion region;

Group III, characterized by the Examiner as drawn to an ESD structure having an island across a length direction of a diffusion region formed at a predetermined angle;

Group IV, characterized by the Examiner as drawn to an ESD structure having an island with a first parallel portion and a second portion skewed portion and connecting at a predetermined angle;

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Group V, characterized by the Examiner as drawn to an ESD structure having an island formed along a length of a diffusion and connected to a node,

Group VI, characterized by the Examiner as drawn to an ESD structure having an island in the first diffusion region in contact with the gate at a predetermined angle and a second island formed in the first diffusion in contact with the first island;

Group VII, characterized by the Examiner as drawn to an ESD structure having a plurality of island portion for blocking implanted ions and a metal bus partially overlapping the islands;

Group VIII, characterized by the Examiner as drawn to an ESD structure having a plurality of islands in contact with the gate, each island having a dendritic structure;

Group IX, characterized by the Examiner as drawn to an ESD structure having a plurality of islands formed along a length with portions of different lengths;

Group X, characterized by the Examiner as drawn to an ESD structure having at least one island having a length greater than 50% of a longitudinal dimension of a channel region and formed symmetrically along the length direction,

Group XI, characterized by the Examiner as drawn to an ESD structure having at least one island having a length greater than 50% of a longitudinal dimension of a channel region and formed non-symmetrically along the length direction; and

Group XII, characterized by the Examiner as drawn to an ESD structure having at least one island having a length greater than 50% of a longitudinal dimension of a channel region and at least two portions formed at predetermined angles to one another.

Applicants provisionally elect Group I. Claims 1-19 read on the elected species.

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Please grant any extensions of time required to enter this response and charge any additional required fees to our deposit account 06-0916.

Respectfully submitted,

FINNEGAN, HENDERSON, FARABOW,  
GARRETT & DUNNER, L.L.P.

Dated: September 20, 2002

By: 

Bryan S. Latham

Reg. No. 49,085

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